

MMBZ16V, SZMMBZ16V

40 Watt Peak Power Zener Transient Voltage Suppressors

SOT-23 Dual Common Anode Zeners for ESD Protection

These dual monolithic silicon Zener diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Features

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range – 15.2 V to 16.80 V
- Peak Power – 40 W @ 1.0 ms (Unidirectional), per Figure 5 Waveform
- ESD Rating:
 - Class 3B (> 16 kV) per the Human Body Model
 - Class C (> 400 V) per the Machine Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Maximum Clamping Voltage @ Peak Pulse Current
- Low Leakage < 5.0 μA
- Flammability Rating UL 94 V-0
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

Mechanical Characteristics

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

Package designed for optimal automated board assembly

Small package size for high density applications

Available in 8 mm Tape and Reel

Use the Device Number to order the 7 inch/3,000 unit reel.

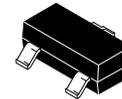
Replace the “T1” with “T3” in the Device Number to order the

13 inch/10,000 unit reel.

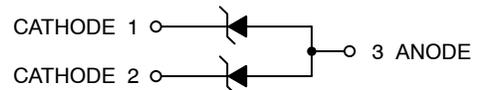


ON Semiconductor®

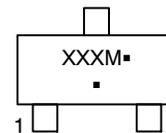
www.onsemi.com



SOT-23
CASE 318
STYLE 12



MARKING DIAGRAM



XXX = Specific Device Code

M = Date Code

▪ = Pb-Free Package

(Note: Microdot may be in either location)

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 2 of this data sheet.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1)	P_{pk}	40	W
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to +150	$^\circ\text{C}$
Lead Solder Temperature - Maximum (10 Second Duration)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 5 and derate above $T_A = 25^\circ\text{C}$ per Figure 6.
2. FR-5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in, 99.5% alumina.

*Other voltages may be available upon request.

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MMBZ16VALT1G	16A	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZMMBZ16VALT1G*	16A		
MMBZ16VTALT1G	16T		
SZMMBZ16VTALT1G*	16T		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

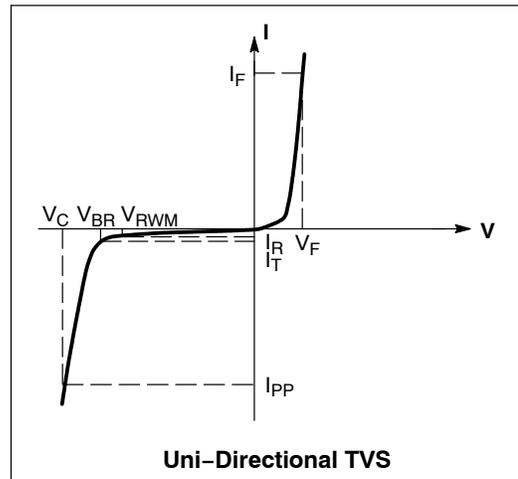
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ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V _{BR}	Breakdown Voltage @ I _T
I _T	Test Current
θV _{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F
Z _{ZT}	Maximum Zener Impedance @ I _{ZT}
I _{ZK}	Reverse Current
Z _{ZK}	Maximum Zener Impedance @ I _{ZK}



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

(V_F = 0.9 V Max @ I_F = 10 mA) (5% Tolerance) **40 WATTS**

Device*	Device Marking	V _{RWM} Volts	I _R @ V _{RWM} nA	Breakdown Voltage				V _C @ I _{PP} (Note 5)		θV _{BR} mV/°C
				V _{BR} (Note 4) (V)			@ I _T mA	V _C V	I _{PP} A	
				Min	Nom	Max				
MMBZ16VALT1G	16A	13	50	15.20	16	16.80	1.0	23	1.7	13.8

(V_F = 0.9 V Max @ I_F = 10 mA) (2% Tolerance) **40 WATTS**

Device*	Device Marking	V _{RWM} Volts	I _R @ V _{RWM} nA	Breakdown Voltage				V _C @ I _{PP} (Note 5)		θV _{BR} mV/°C
				V _{BR} (Note 4) (V)			@ I _T mA	V _C V	I _{PP} A	
				Min	Nom	Max				
MMBZ16VTALT1G	16T	13	50	15.68	16	16.32	1.0	23	1.7	13.8

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.

5. Surge current waveform per Figure 5 and derate per Figure 6

* Include SZ-prefix devices where applicable.

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TYPICAL CHARACTERISTICS

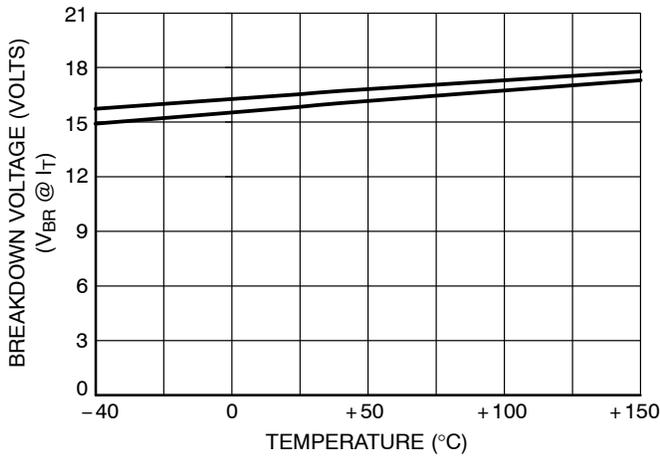


Figure 1. Typical Breakdown Voltage versus Temperature

(Upper curve is for bidirectional mode, lower curve is for unidirectional mode)

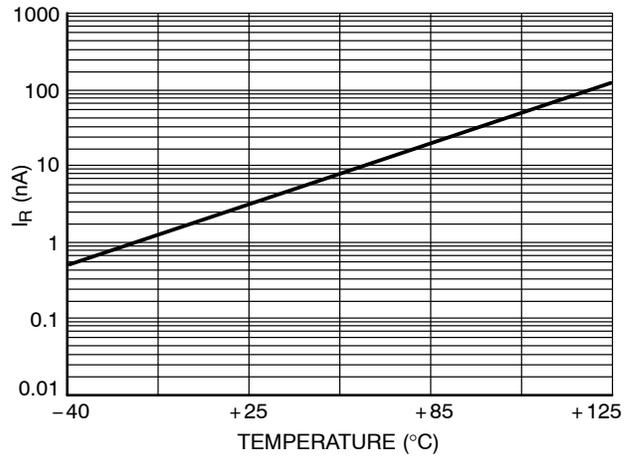


Figure 2. Typical Leakage Current versus Temperature

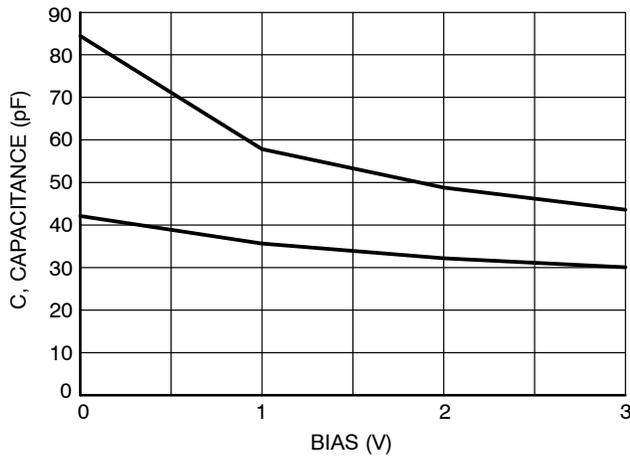


Figure 3. Typical Capacitance versus Bias Voltage

(Upper curve is for unidirectional mode, lower curve is for bidirectional mode)

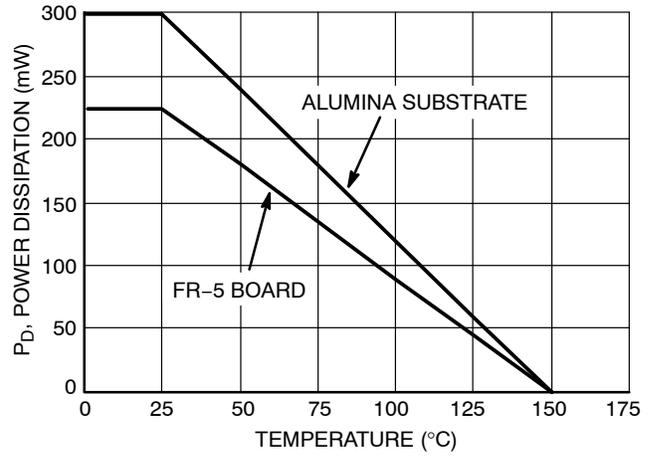


Figure 4. Steady State Power Derating Curve

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TYPICAL CHARACTERISTICS

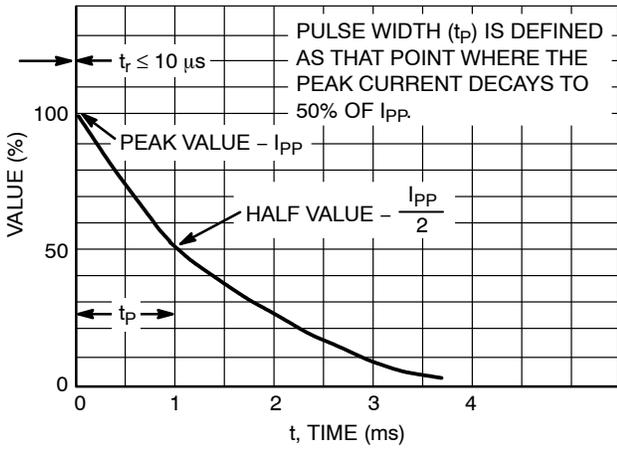


Figure 5. Pulse Waveform

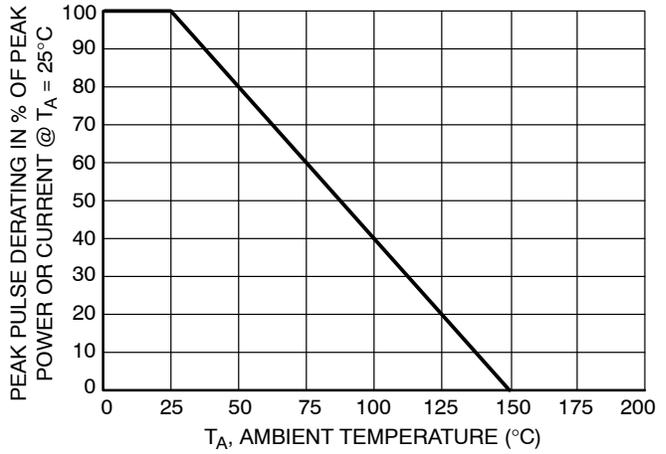


Figure 6. Pulse Derating Curve

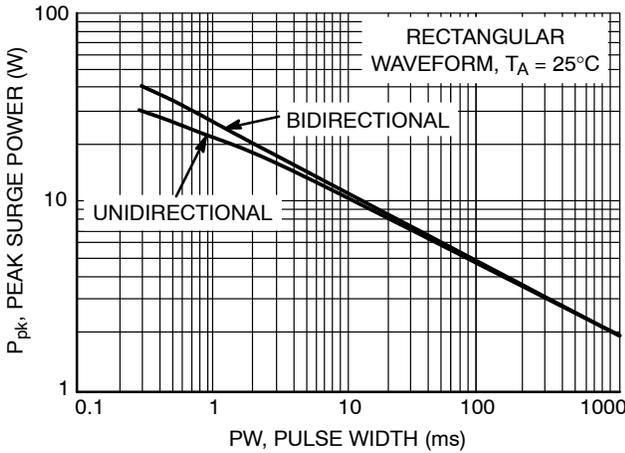


Figure 7. Maximum Non-repetitive Surge Power, P_{pk} versus PW

Power is defined as $V_{RSM} \times I_{Z(pk)}$ where V_{RSM} is the clamping voltage at $I_{Z(pk)}$.

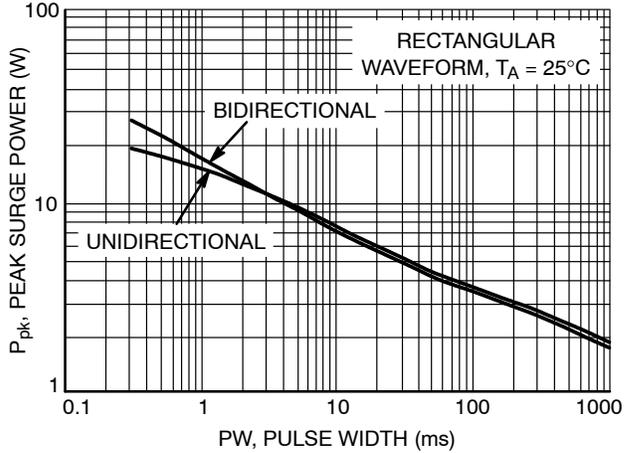


Figure 8. Maximum Non-repetitive Surge Power, $P_{pk(NOM)}$ versus PW

Power is defined as $V_Z(NOM) \times I_{Z(pk)}$ where $V_Z(NOM)$ is the nominal Zener voltage measured at the low test current used for voltage classification.

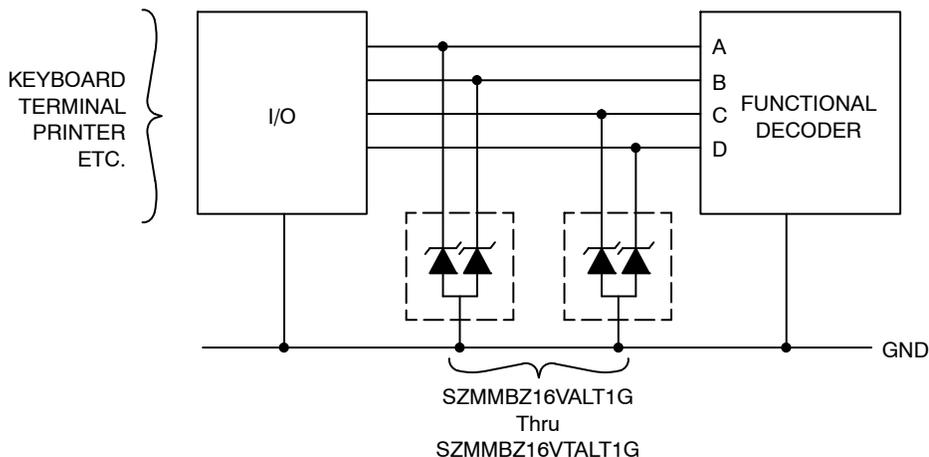
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TYPICAL COMMON ANODE APPLICATIONS

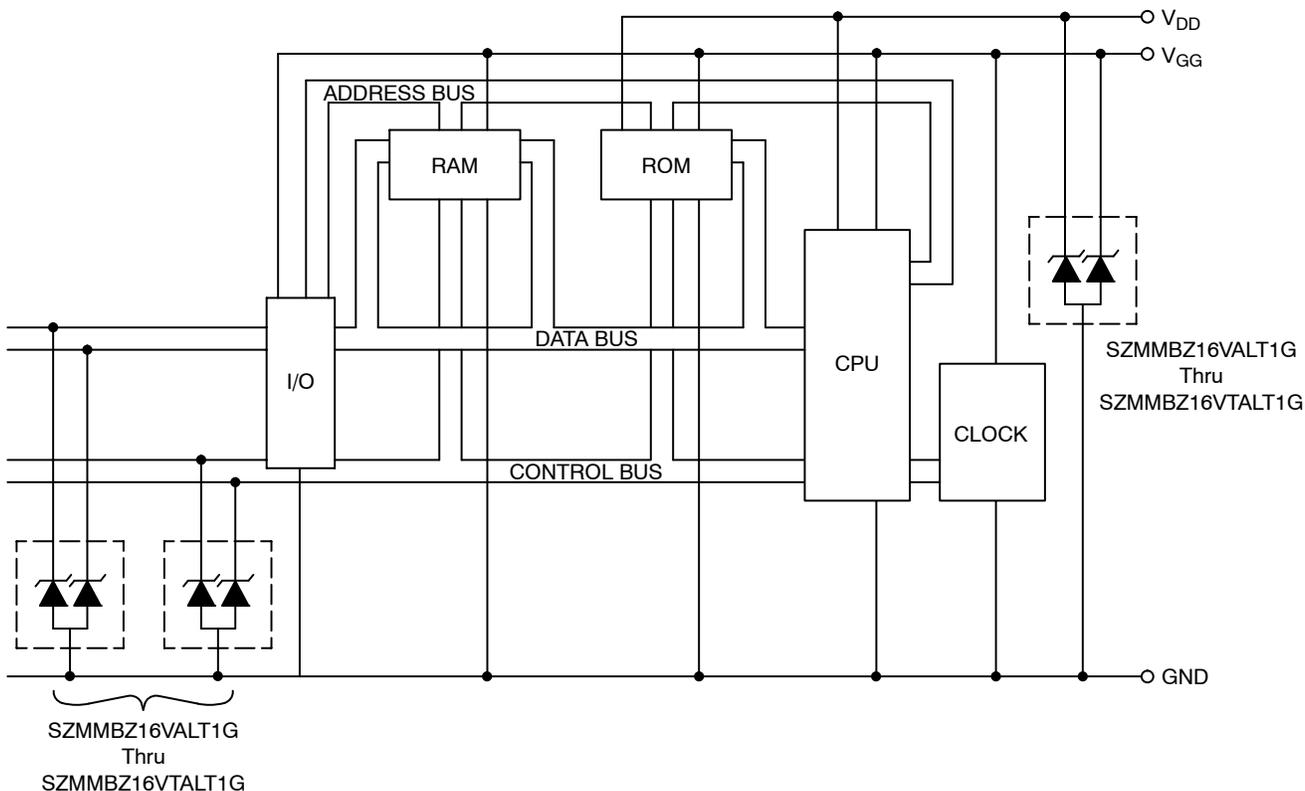
A dual junction common anode design in a SOT-23 package protects two separate lines using only one package. This adds flexibility and creativity to PCB design especially

when board space is at a premium. Two simplified examples of TVS applications are illustrated below.

Computer Interface Protection



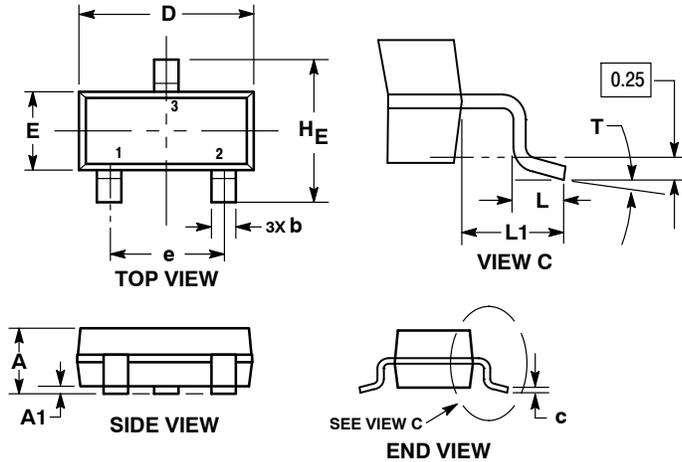
Microprocessor Protection



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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR



NOTES:

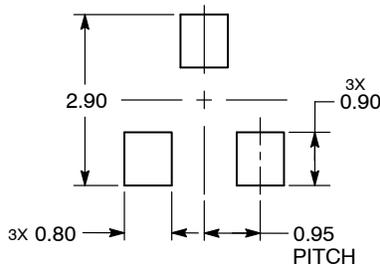
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 12:

1. CATHODE
2. CATHODE
3. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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